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L Number	Hits	Search Text	DB	Time stamp
2	3	("6238735") or ("5954878") or ("5670210").PN.	USPAT; US-PGPUB; EPO; JPO	2003/01/09 11:42
3	2	("6191053").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/01/09 13:44
4	2	("20020004100").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/01/09 13:53
6	2	(("20020004100").PN.) and (control adj gas)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/01/09 14:20
7	0	(("20010001746").PN.) and (control adj gas)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/01/09 14:12
8	2	((("20020004100").PN.) and (control adj gas)) and (control with solvent)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/01/09 14:17
9	1	((("20020004100").PN.) and (control adj gas)) and (concentration)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/01/09 14:20
10	0	((("20010001746").PN.) and (concentration))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/01/09 13:58
5	2	("20010001746").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/01/09 13:59
11	0	((("20010001746").PN.) and (gas))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/01/09 14:13
12	1	((("20010001746").PN.) and (vapor))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/01/09 14:13
13	1	((("20010001746").PN.) and (air))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/01/09 14:16
14	2	6238735.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/01/09 14:16
15	2	6238735.pn. and (control adj gas)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/01/09 14:16
16	2	(6238735.pn. and (control adj gas)) and (control with solvent)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/01/09 14:17
17	2	((6238735.pn. and (control adj gas)) and (control with solvent)) and (concentration)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/01/09 14:17

18	3	((("6238735") or ("5954878") or ("5670210")).PN.) and (control adj gas)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/01/09 14:20
19	0	(("6191053").PN.) and (control adj gas)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/01/09 14:26
20	0	(("6191053").PN.) and (concentration)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/01/09 14:23
21	1	((("6191053").PN.) and (vapor)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/01/09 14:23
22	2	5954878.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/01/09 14:23
23	1	5954878.pn. and (vapor)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/01/09 14:26
24	2	5954878.pn. and (control adj gas)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/01/09 14:23
25	1	(5954878.pn. and (control adj gas)) and (concentration)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/01/09 14:25
26	2	5238713.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/01/09 14:26
27	0	5238713.pn. and (concentration)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/01/09 14:26
28	0	5238713.pn. and (control adj gas)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/01/09 14:26
29	0	5238713.pn. and (vapor)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/01/09 14:26
30	2	5180431.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/01/09 14:26
31	0	5180431.pn. and (concentration)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/01/09 14:26
32	0	5180431.pn. and (control adj gas)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/01/09 14:26
33	0	5180431.pn. and (vapor)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/01/09 14:26

34	2	5180431.pn. and (air or gas)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/01/09 14:27
35	2	5238713.pn. and (air or gas)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/01/09 14:28
36	17239	(solvent with (gas or vapor or air)) and (semiconductor or photoresist or resist or polymer) and (coating or extruded or extrusion or rotating or rotate)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/01/09 14:35
37	1416	((solvent with (gas or vapor or air)) and (semiconductor or photoresist or resist or polymer) and (coating or extruded or extrusion or rotating or rotate)) and wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/01/09 14:35
38	1137	((((solvent with (gas or vapor or air)) and (semiconductor or photoresist or resist or polymer) and (coating or extruded or extrusion or rotating or rotate)) and wafer) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/01/09 14:35
39	685	(((solvent with (gas or vapor or air)) and (semiconductor or photoresist or resist or polymer) and (coating or extruded or extrusion or rotating or rotate)) and wafer) and semiconductor) and (photoresist or resist)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/01/09 14:35
40	141	((((solvent with (gas or vapor or air)) and (semiconductor or photoresist or resist or polymer) and (coating or extruded or extrusion or rotating or rotate)) and wafer) and semiconductor) and (photoresist or resist)) and (solvent with concentration)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/01/09 14:36
41	57	((((((solvent with (gas or vapor or air)) and (semiconductor or photoresist or resist or polymer) and (coating or extruded or extrusion or rotating or rotate)) and wafer) and semiconductor) and (photoresist or resist)) and (solvent with concentration)) and (gas same concentration)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/01/09 14:37